

isc N-Channel MOSFET Transistor

2SK843

DESCRIPTION

- Drain Current –I_D=10A@ T_C=25 $^\circ\!\!\mathrm{C}$
- Drain Source Voltage-
- : V_{DSS}= 60V(Min)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

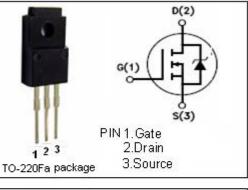


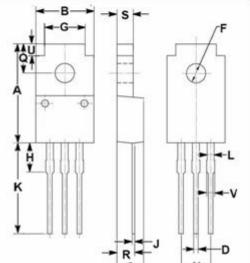
High speed power switching

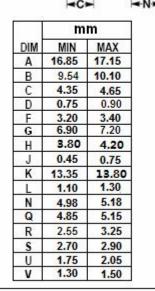
ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	60	V
V _{GS}	Gate-Source Voltage	±20	V
ID	Drain Current-continuous@ TC=25℃	10	A
P _{tot}	Total Dissipation@TC=25°C	40	W
Tj	Max. Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C

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SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT			
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	60			V			
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =0; I _D =1mA	2.0		4.0	V			
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D = 5A			0.1	Ω			
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±16V;V _{DS} = 0			±10	uA			
IDSS	Zero Gate Voltage Drain Current	V _{DS} =60V; V _{GS} = 0			250	uA			

• ELECTRICAL CHARACTERISTICS (Tc=25°C)

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